



NDF10N60ZG Information



For Reference Only

Part Number NDF10N60ZG
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 10A TO-220FP

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NDF10N60ZG Specifications

Manufacturer Part Number NDF10N60ZG Manufacturer ON Semiconductor Category Discrete Semiconductor Products Package TO-220-3 Full Pack Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 100µA Gate Charge (Qg) (Max) @ Vgs 68nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1645pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 39W (Tc) Rds On (Max) @ Id, Vgs 750 mOhm @ 5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-220-3 Full Pack Series TO-220-3 Full Pack FET Type N-Channel Technology MOSFET (Metal Oxide) Tourin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole	Manufacturer Part Number	NDF10N60ZG
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Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 750 mOhm @ 5A, 10V Operating Temperature Operating Type Through Hole	Vgs(th) (Max) @ Id	4.5V @ 100μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)39W (Tc)Rds On (Max) @ Id, Vgs750 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Gate Charge (Qg) (Max) @ Vgs	68nC @ 10V
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Rds On (Max) @ Id, Vgs750 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole	Power Dissipation (Max)	39W (Tc)
Mounting Type Through Hole	Rds On (Max) @ Id, Vgs	750 mOhm @ 5A, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Supplier Device Package TO-220FP	Mounting Type	Through Hole
	Supplier Device Package	TO-220FP
Package / Case TO-220-3 Full Pack	Package / Case	TO-220-3 Full Pack
Report errors?		Report errors?

NDF10N60ZG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NDF10N60ZG Payment Methods





















NDF10N60ZG Shipping Methods













If you have any question about NDF10N60ZG, please do not hesitate to contact us!

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